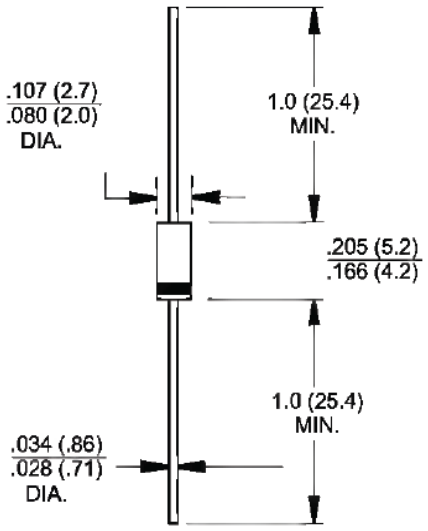
TAIWAN SEMICONDUCTOR

RoHS COMPLIANCE

HER101 - HER108

1.0AMP High Efficient Rectifiers

DO-41



Features

- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ Low power loss
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Case: Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: Color band denotes cathode
- ✧ High temperature soldering guaranteed: 260℃/10s /.375", (9.5mm) lead lengths at 5 lbs, (2.3kg) tension
- ✧ Weight: 0.34 grams

Dimensions in inches and (millimeters)

Marking Diagram

HER10X	= Specific Device Code
G	= Green Compound
Y	= Year
WW	= Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	HER 101	HER 102	HER 103	HER 104	HER 105	HER 106	HER 107	HER 108	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375 (9.5mm) Lead Length @ T_A=55℃	$I_{F(AV)}$	1								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30								A
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	1.0				1.3	1.7			V
Maximum Reverse Current @ Rated VR T_A=25 ℃ T_A=125 ℃	I_R	5 150								uA
Maximum Reverse Recovery Time (Note 2)	Trr	50					75			nS
Typical Junction Capacitance (Note 3)	Cj	25					20			pF
Typical Thermal Resistance (Note 4)	$R_{\theta jA}$ $R_{\theta jC}$ $R_{\theta jL}$	70 15 25								^{O}C/W
Operating Temperature Range	T_J	- 65 to + 150								^{O}C
Storage Temperature Range	T_{STG}	- 65 to + 150								^{O}C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

Note 4: Mount on Cu-Pad Size 16mm x 16mm on PCB

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RATINGS AND CHARACTERISTIC CURVES (HER101 THRU HER108)

FIG.1 FORWARD CURRENT DERATING CURVE

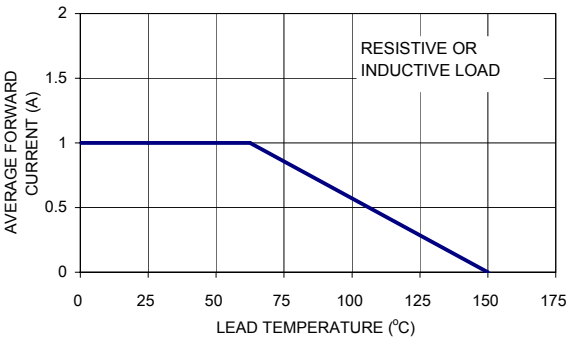


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

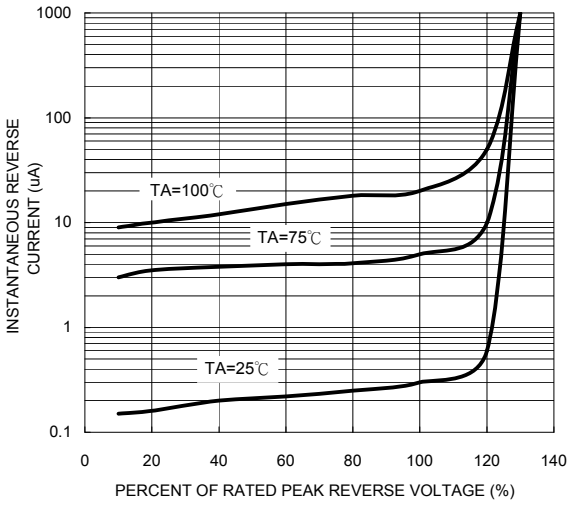


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

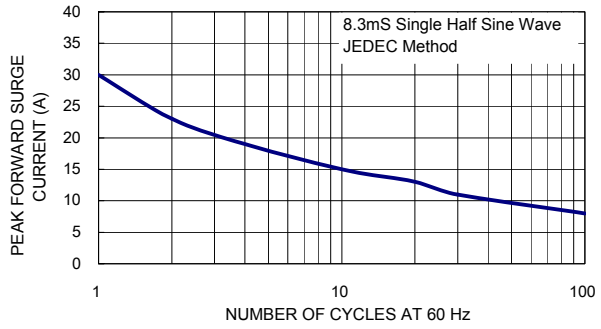


FIG. 5 TYPICAL FORWARD CHARACTERISRICS

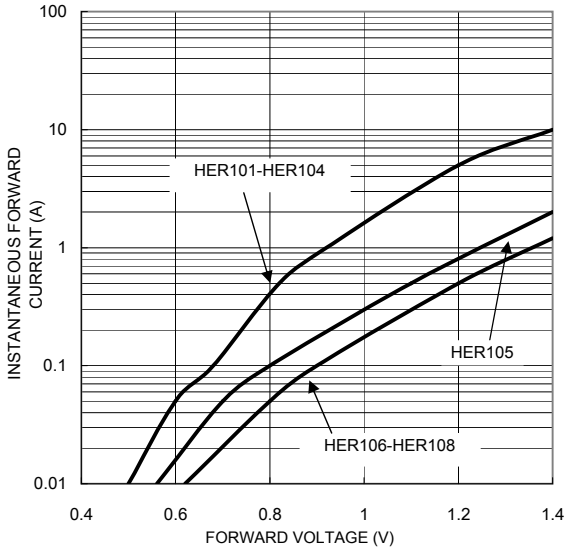


FIG. 4 TYPICAL JUNCTION CAPACITANCE

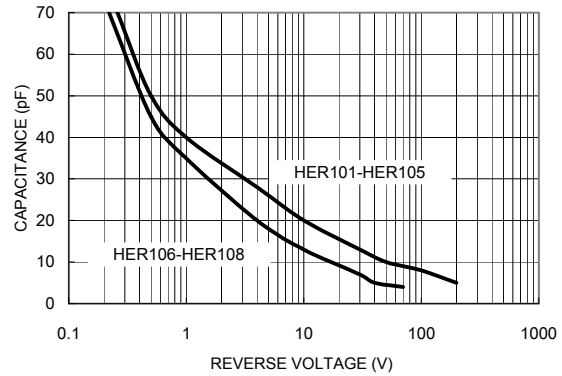
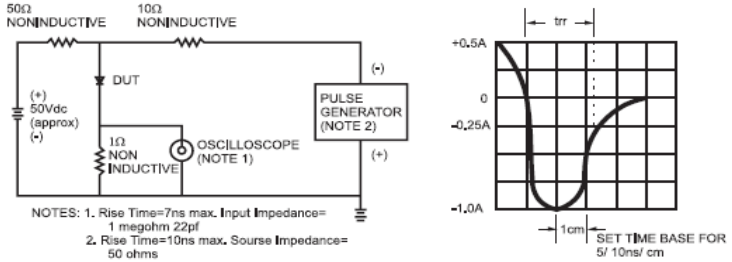


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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